

# Electrodeionization (EDI)

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# Outline

- Process Principles
- EDI History
- Applications and Benefits
- Performance
- Feed Water Requirements and Pretreatment

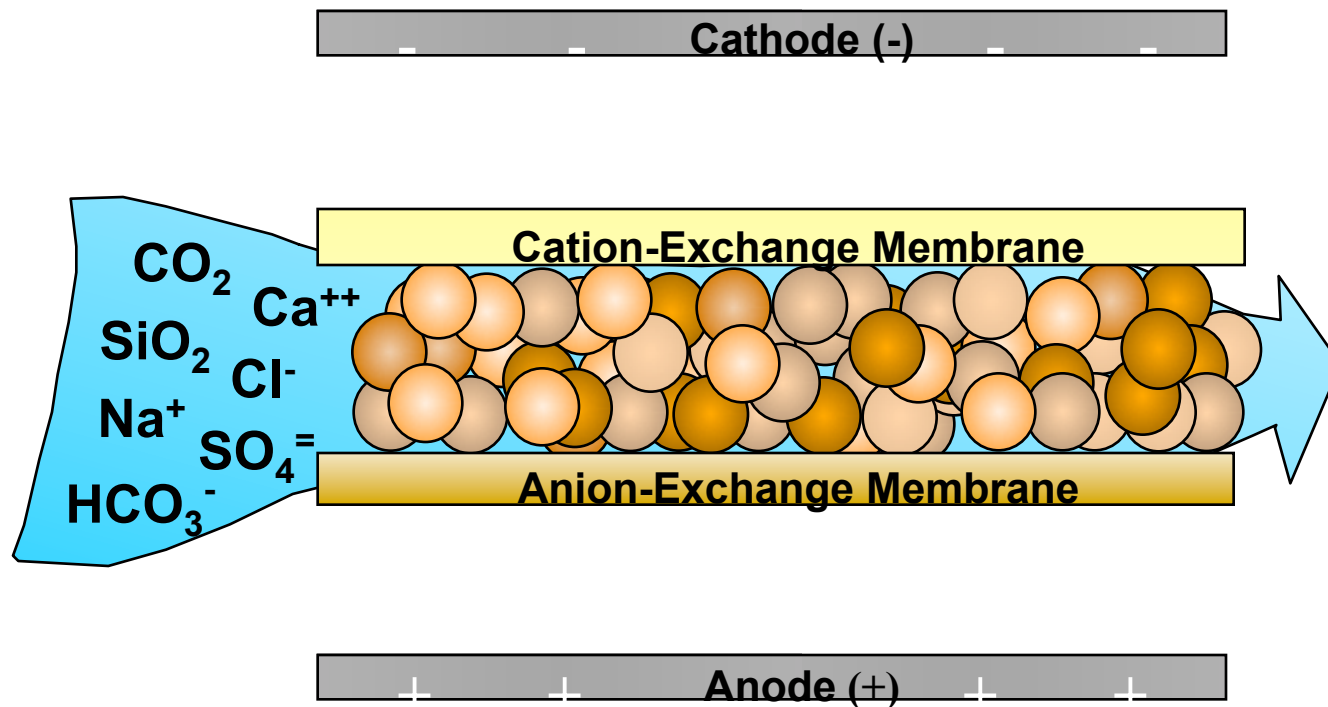
# Process Principles

# Process Principles

## Device

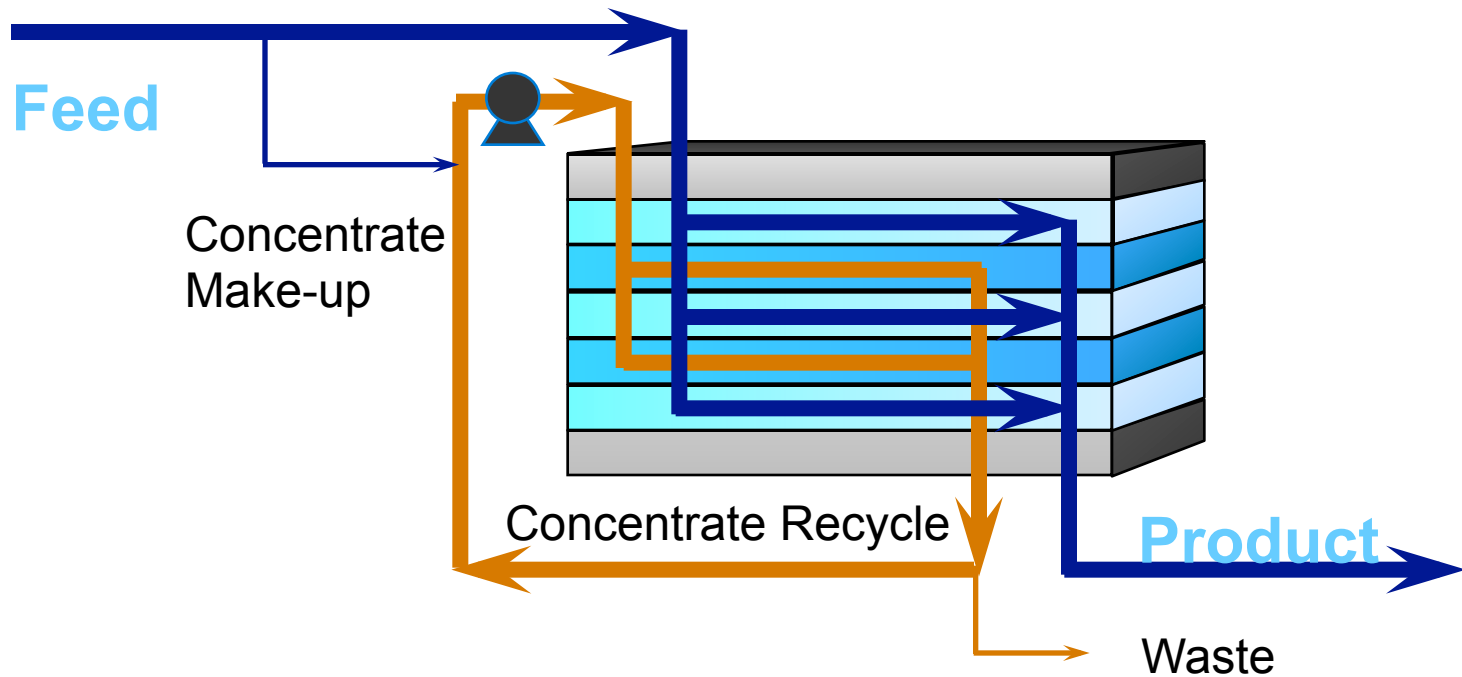
- Cation exchange membrane
- Anion exchange membrane
- Spacers
- Electrodes
- Ion exchange resin

# Process Principles



# Process Principles

## EDI System



# Process Principles

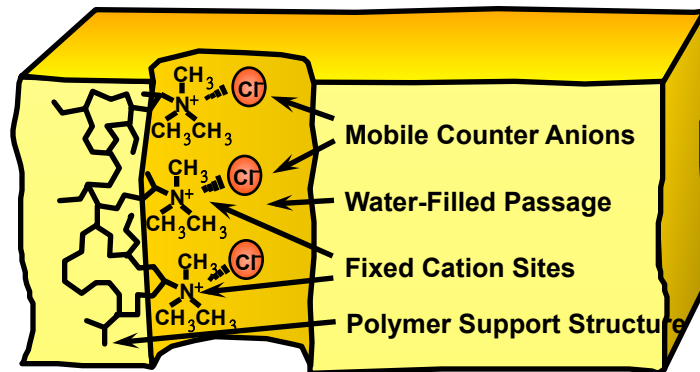
## How does EDI work?

- Enhanced transfer regime (high salinity)
  - Remove strong ions from water
- Electroregeneration regime (low salinity)
  - Remove ionizable species (weak acids or weak bases) from water

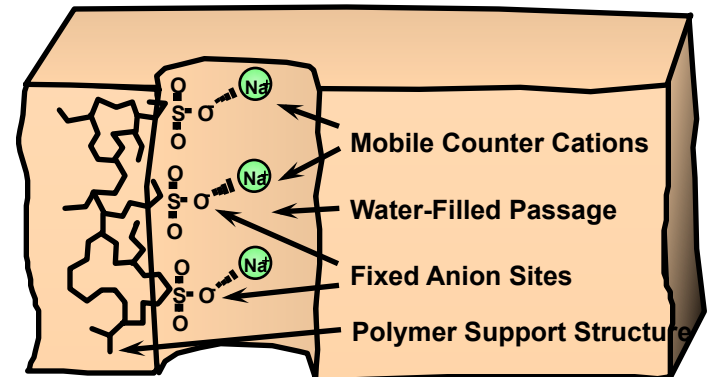
# PROCESS PRINCIPLES

## Ion-Exchange Membrane

**Anion-Exchange Membrane**

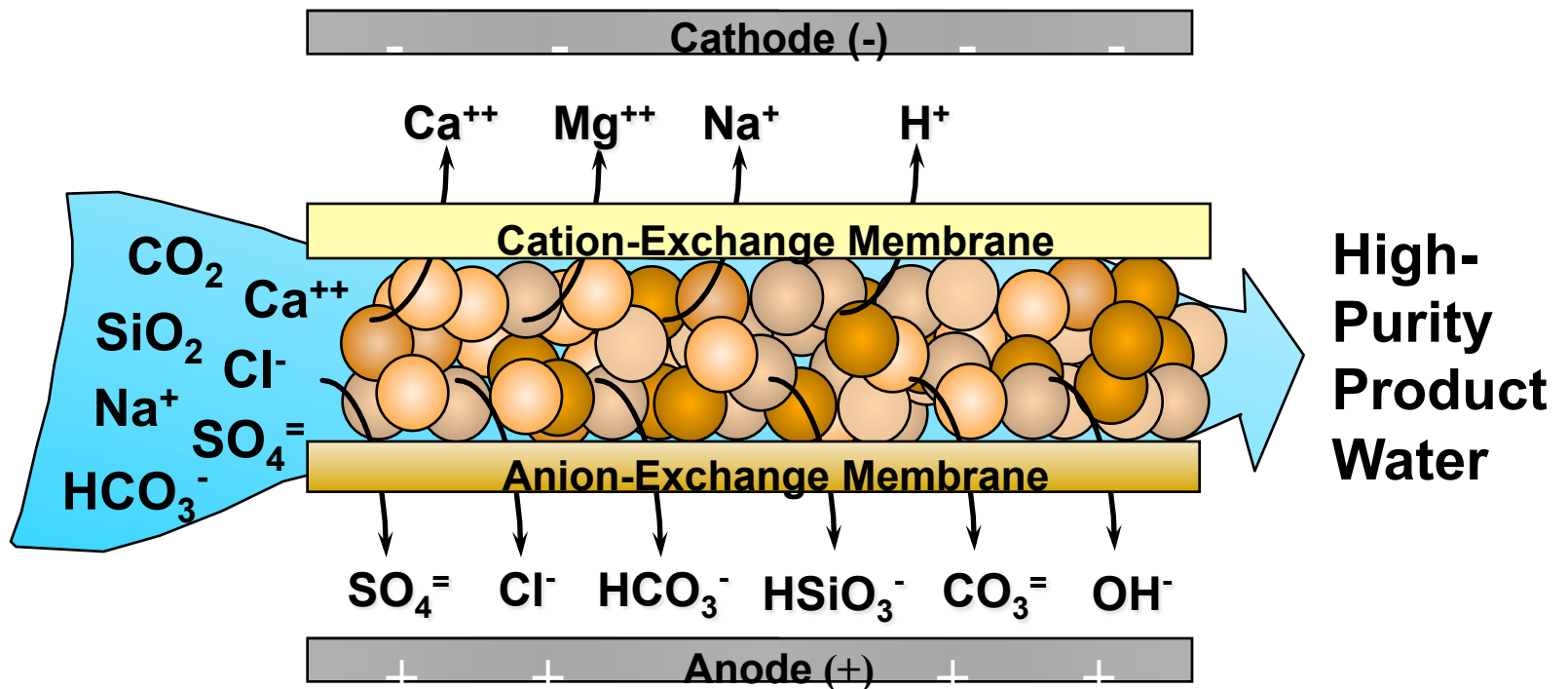


**Cation-Exchange Membrane**





# Process Principles



# Process Principles

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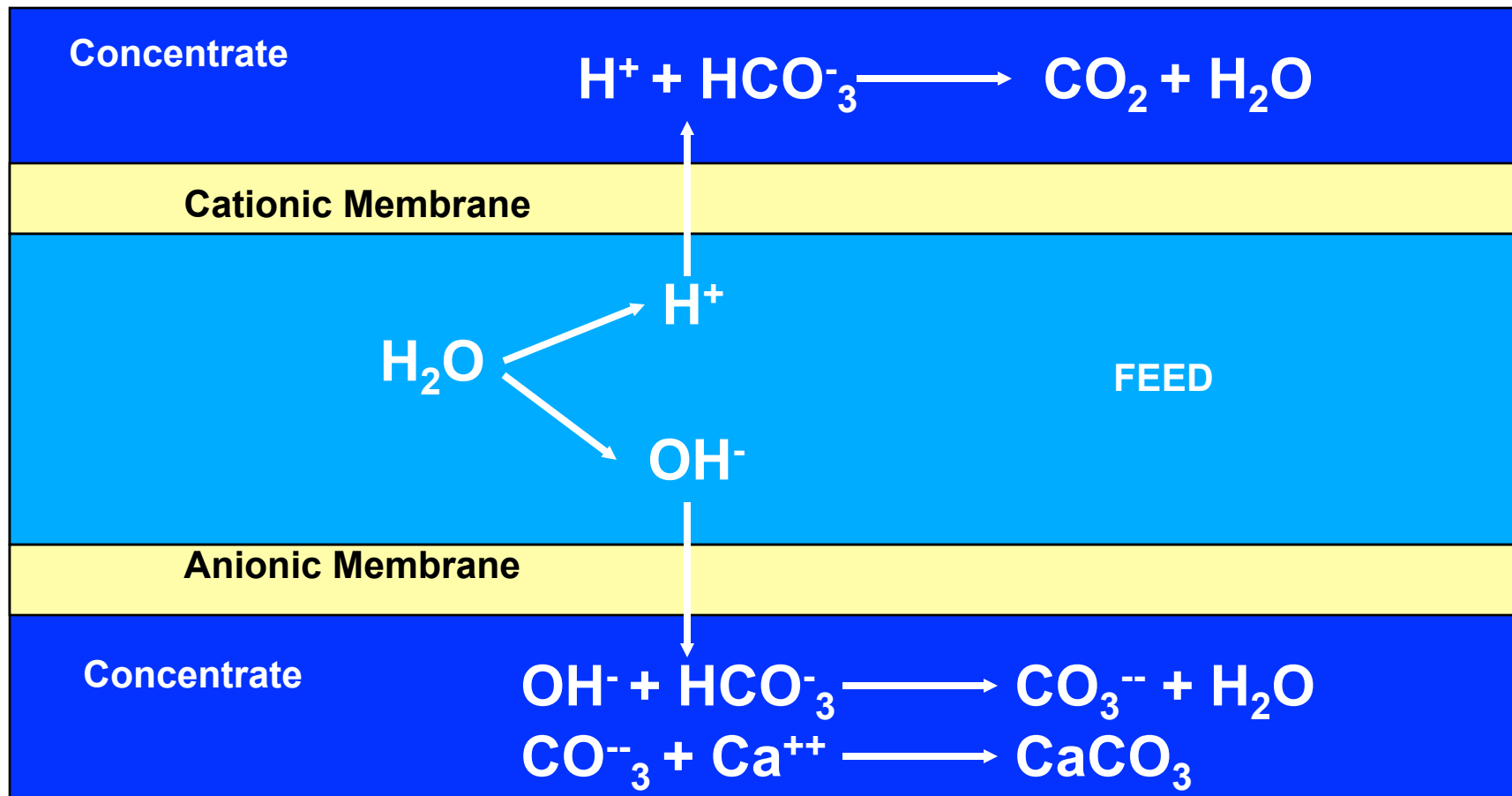
## Enhanced transfer regime

Ions are transferred from solution to resins by diffusion.

Ions move inside resins by means of electricity

Ions reach the membranes and pass to the brine flow.

# Polarization

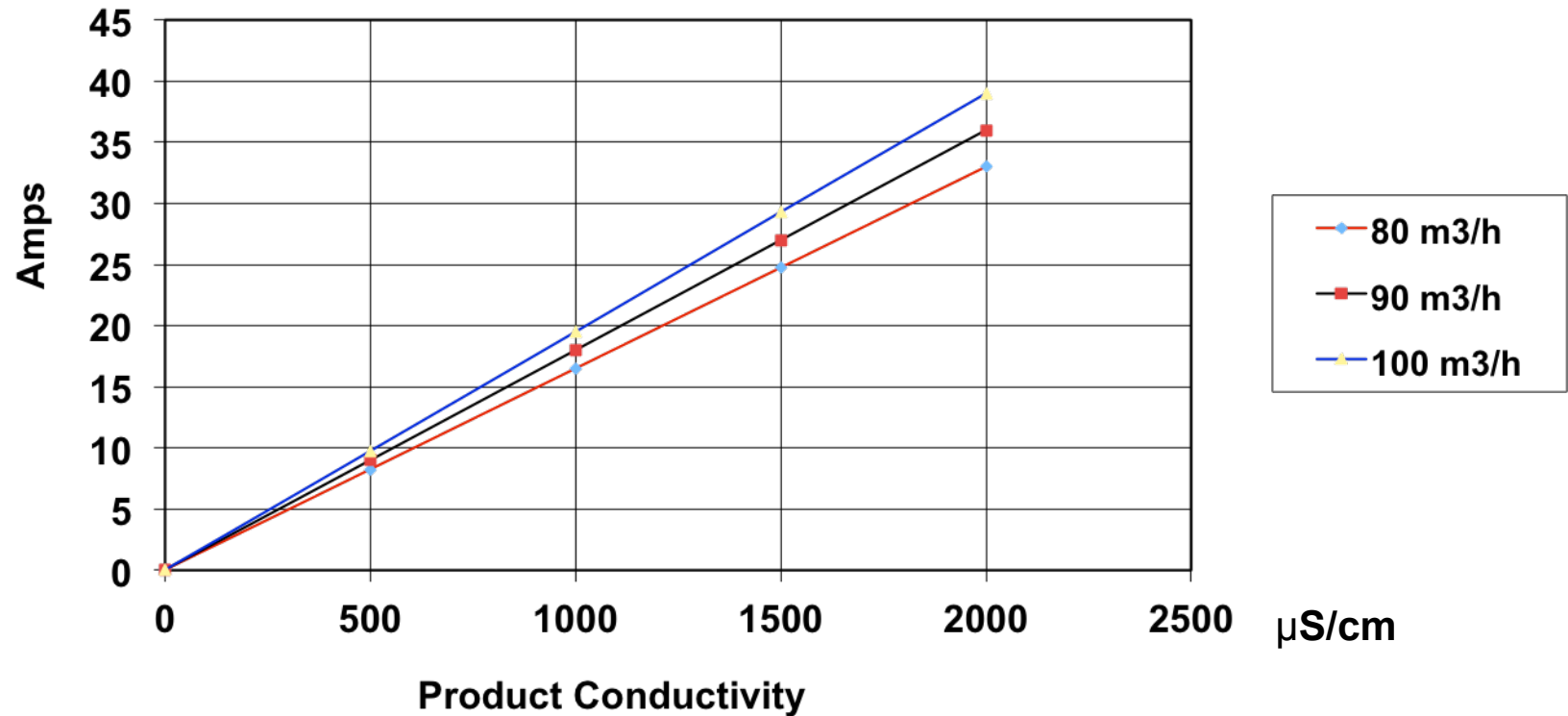


# Process Principles

## Electro regeneration Regime

- Resin in hydrogen and hydroxide forms
- Removal of weakly ionized compounds by ionization reactions
  - $\text{CO}_2 + \text{OH}^- \rightarrow \text{HCO}_3^-$        $\text{pK}_a = 6.4$
  - $\text{HCO}_3^- + \text{OH}^- \rightarrow \text{CO}_3^{2-}$        $\text{pK}_a = 10.3$
  - $\text{SiO}_2 + \text{OH}^- \rightarrow \text{HSiO}_3^-$        $\text{pK}_a = 9.8$
  - $\text{H}_3\text{BO}_3 + \text{OH}^- \rightarrow \text{B(OH)}_4^-$        $\text{pK}_a = 9.2$
  - $\text{NH}_3 + \text{H}^+ \rightarrow \text{NH}_4^+$        $\text{pK}_a = 9.2$

# Polarization



# EDI History

# EDI Technology History

- 1955 - Walters et al, work with periodic electro-regeneration of ion exchange resin in stack.
- 1957 - Kollsman patent on basic EDI method and apparatus.
- 1959 - Gluekauf, early EDI experimental data and theory.
- 1960's - Early Ionics EDI experiments.
- 1987 - Millipore Commercialized EDI - "CDI".

# **Applications and Benefits**



# EDI Applications

- Microelectronics
- Power Generation
- Boiler Feed
- Pharmaceutical
- Industrial
- Others

# Technology Benefits

- Continuous process with constant stable product quality.
- No acid or caustic regenerants required
- No upsets or downtime from regeneration
- No need for high purity water rinse and backwash
- Produces high purity water with high water recovery (95%).

# Additional Technology Benefits

- No regeneration waste
- Eliminates need for a waste treatment plant
- Eliminates acid and caustic storage tank
- Eliminates acid and caustic dilution skid
- Reduced floor space
- Safe and reliable (No chemical handling)

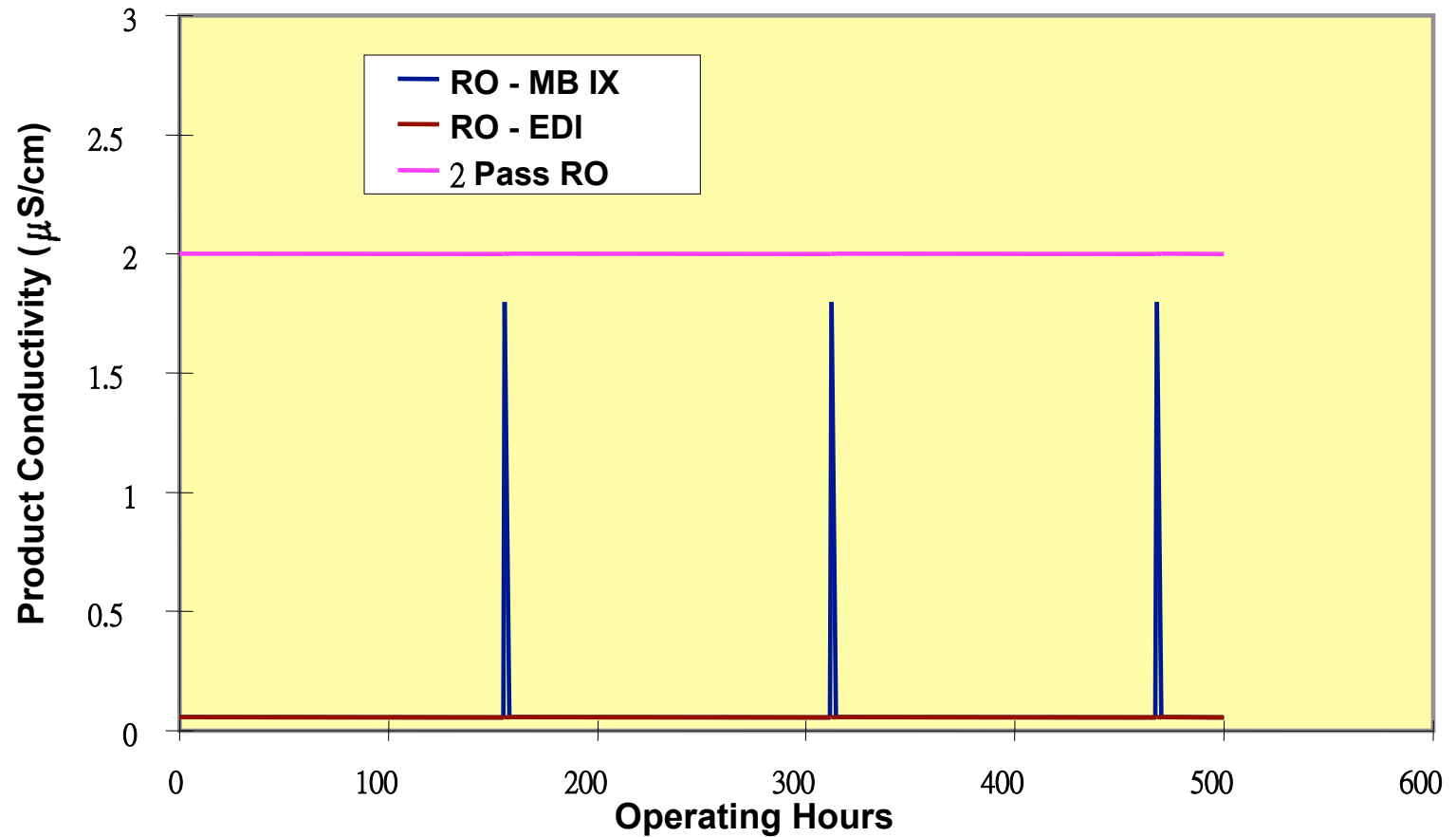
# Additional Technology Benefits

- Minimizing on-going O&M costs
  - essentially no chemical usage
  - minimal maintenance
- Easy to install
  - lower installation costs than with conventional ion-exchange
  - on-line quicker
- Provide consistent high percentage boron rejection

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# **Weakly Ionized Species Removal By EDI**

# Product Quality Comparison



# Boron Removal by EDI

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- Boron present at very low concentrations in many waters
- Presence of Boron often unchecked
- Boron can cause problems in semiconductor manufacturing

# Boron Removal by RO

- Boron removal by RO is pH dependent
- RO does not reject Boron well at neutral pHs due to:
  - poor ionization of boric acid
  - extremely small boric acid molecule
- Typical Boron rejection by RO:
  - 50% to 80% at neutral pH
  - >90% when > pH10

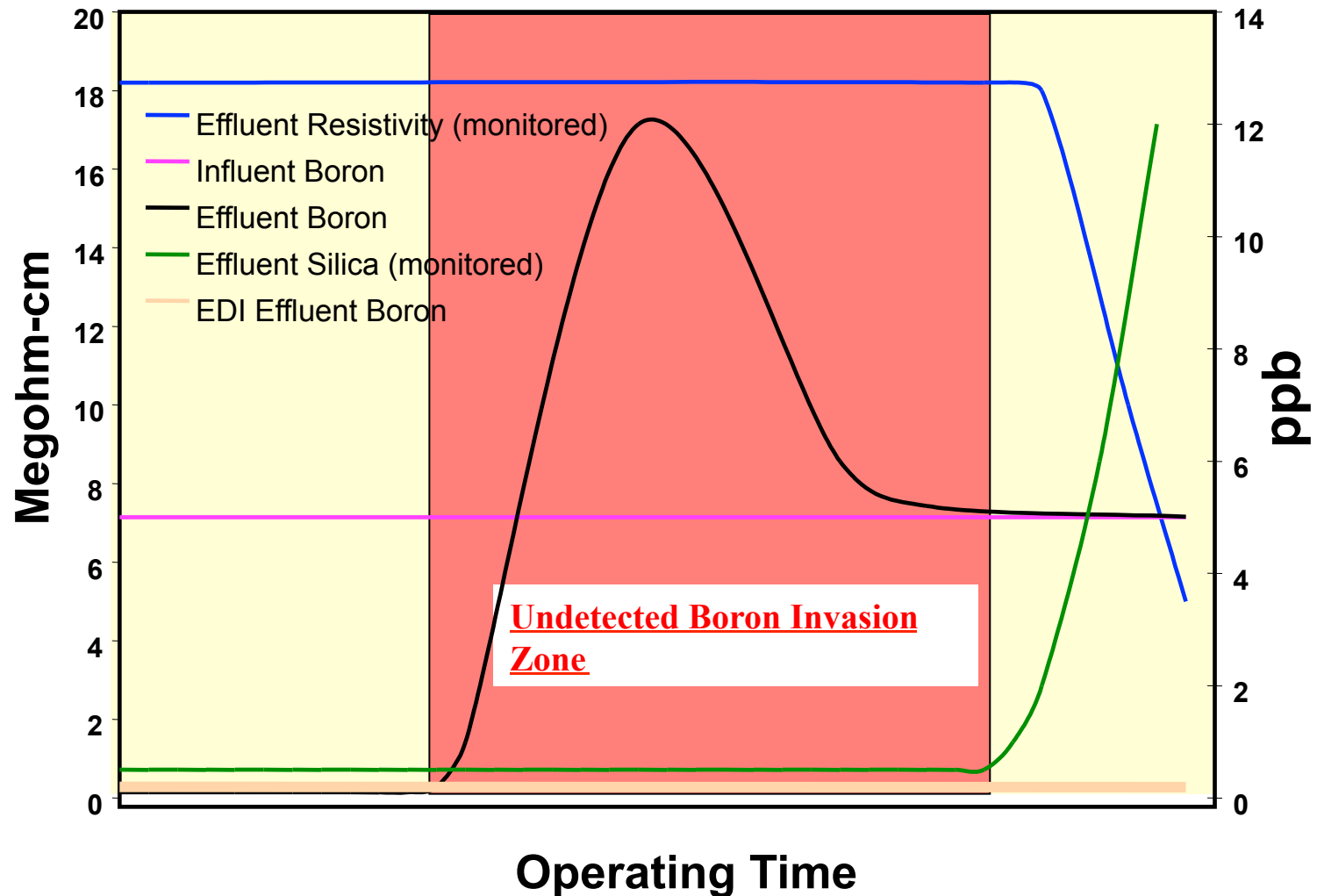


# Boron Removal by Ion-Exchange

- Boron is not well removed by ion-exchange due to:
  - low selectivity
  - poor ionization of boric acid
- Boron is the first to break through ion-exchange
- Studies show Boron breaks through at 20% to 50% of silica run-length
- Boron displacement produces Boron spikes in product water

# Performance of Mixed-Bed Ion-Exchange

(Boron Break-through could effect wafer yield)



# Boron Removal By EDI

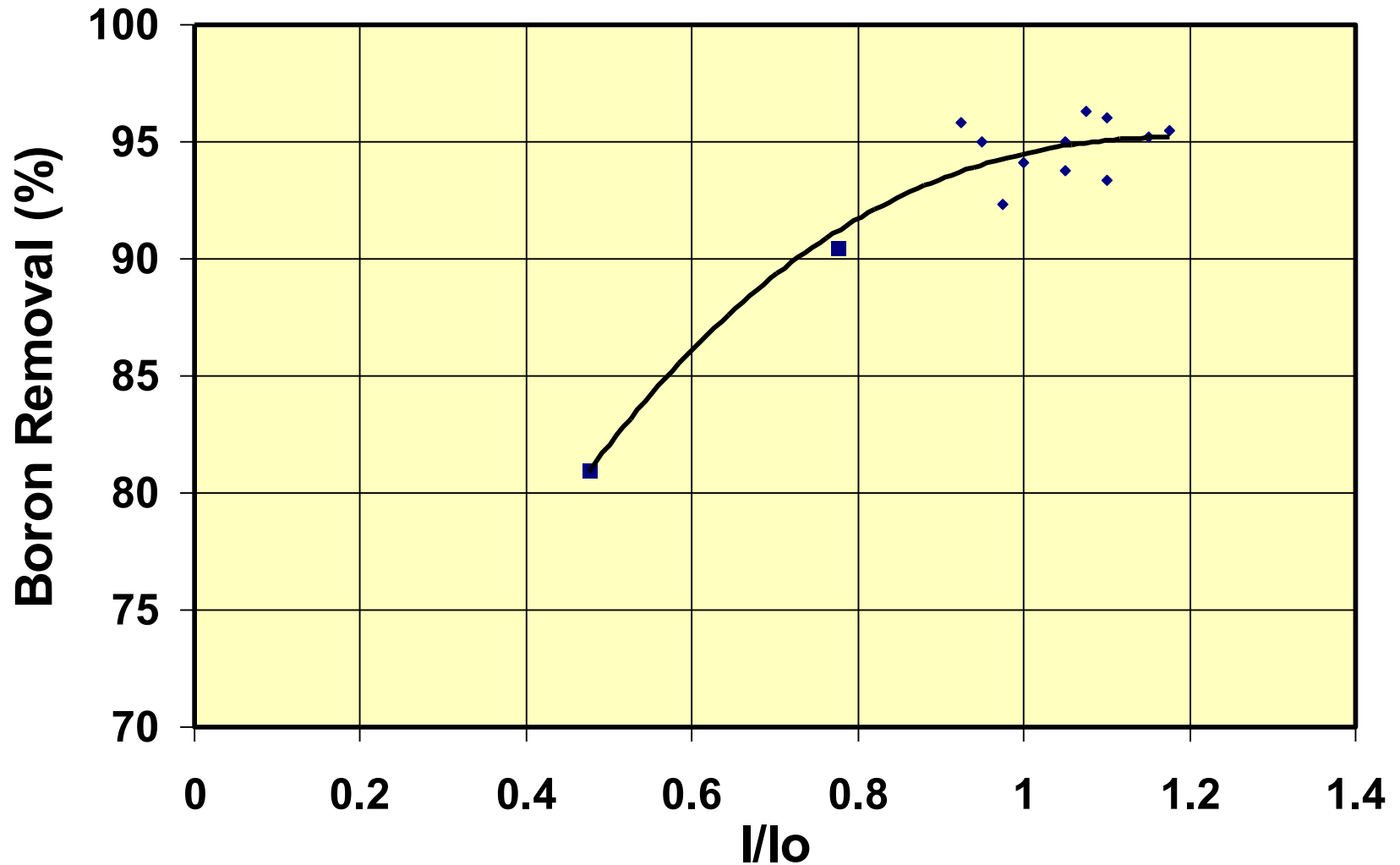
- One of the most effective process to removal boron
- Well designed EDI will provide 96% to 99% boron rejection consistently



# Boron Levels and Removal by RO and EDI

	Feed B (ppb)	Product B (ppb)	B Removal by EDI (%)	B Removal by RO (%)
Semiconductor Plant #2	71	2.75	96.8	39.3
Semiconductor Plant #3	83.5	2.8	96.1	24.1
Semiconductor Plant #4	64.4	0.74	96.6	24.1
Semiconductor Plant #5	2.5	<0.1	>96.0	34.2

# EDI Boron Removal at Varying Current Density



# Silica Removal by EDI

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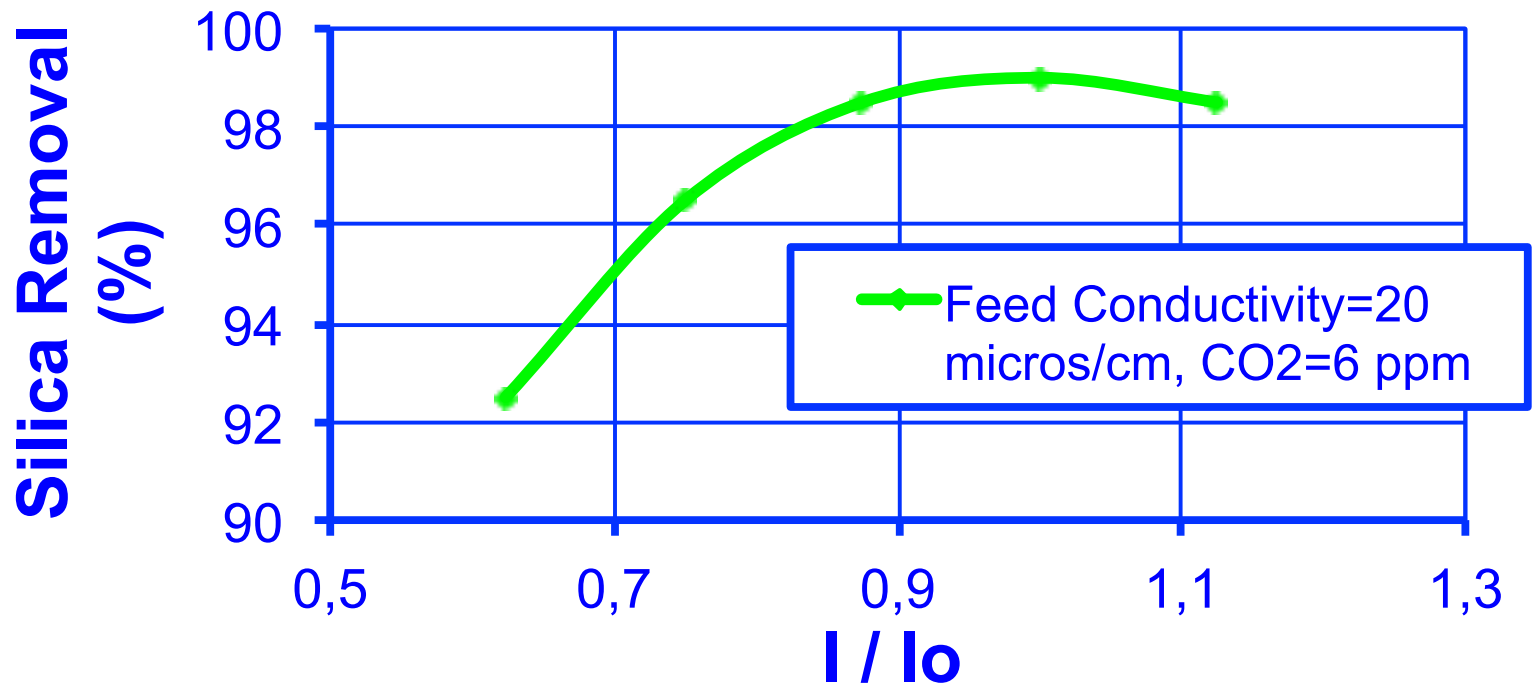
Silica removal is critical for semiconductor manufacturing

- high silica levels lead to expensive chip failures
- spec. limited by the ability of instrumentation

# Silica Levels and Removal by EDI

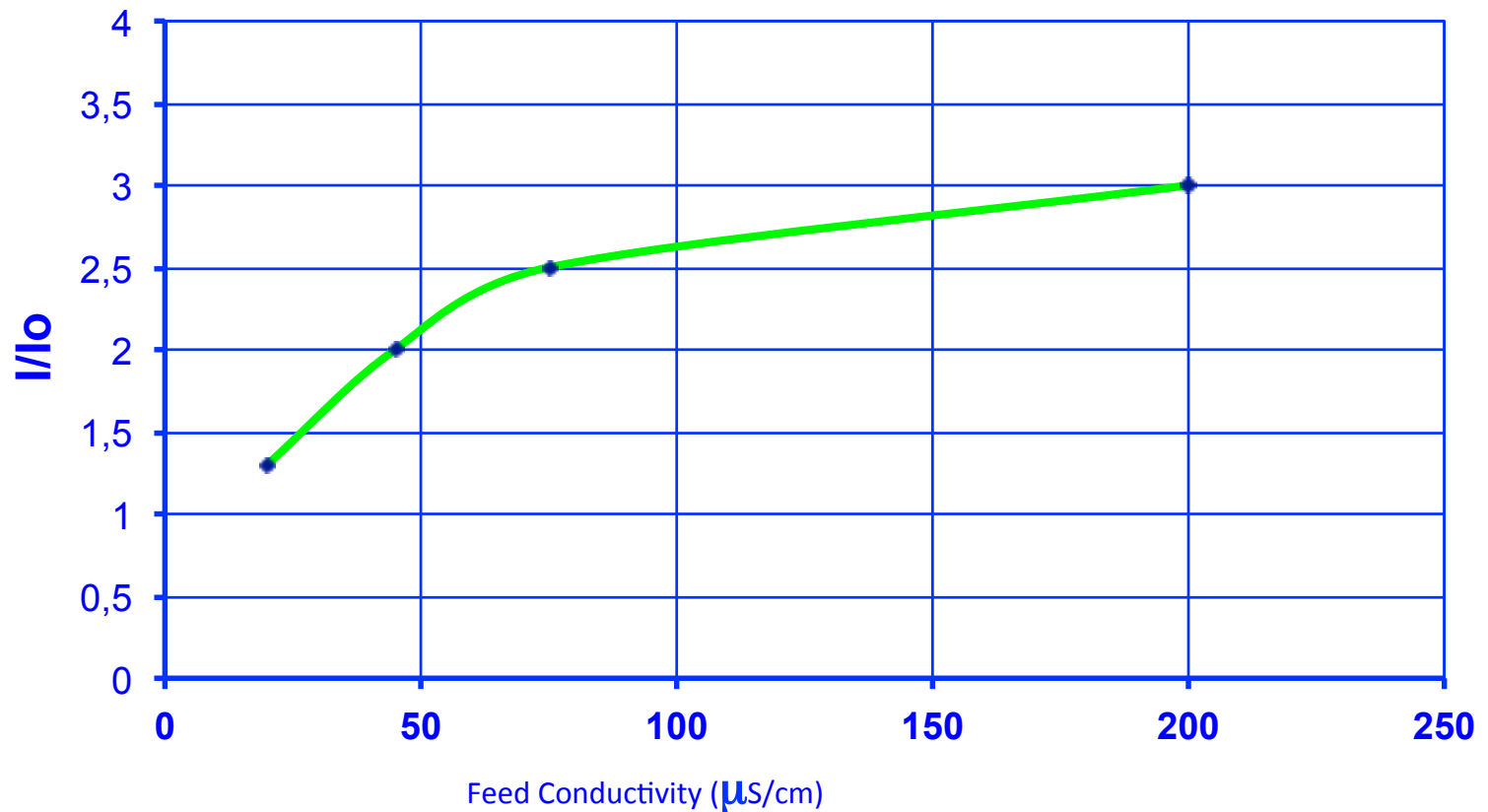
	Feed SiO <sub>2</sub> (ppb)	Product SiO <sub>2</sub> (ppb)	SiO <sub>2</sub> Removal (%)
Semiconductor Plant #1	642	3.1	99.5
Semiconductor Plant #2	181	2.8	98.5
Semiconductor Plant #3	393	<2	>99.5
Semiconductor Plant #4	274	2.6	99.1
Semiconductor Plant #5	650	<5	>99.2

## Study 2: EDI Performance at Varying Current Density





## Study 3: Current Densities Required to Maintain >98.5% Silica Removal



# Carbon Dioxide Removal by EDI

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- Carbon dioxide is often largest load on ion-exchange beds, especially after an RO
- Not effectively removed by other membrane demineralization processes such as RO or ED unless chemical adjustments are made
- Removed >99% by EDI

## CO<sub>2</sub> Levels and Removal by EDI

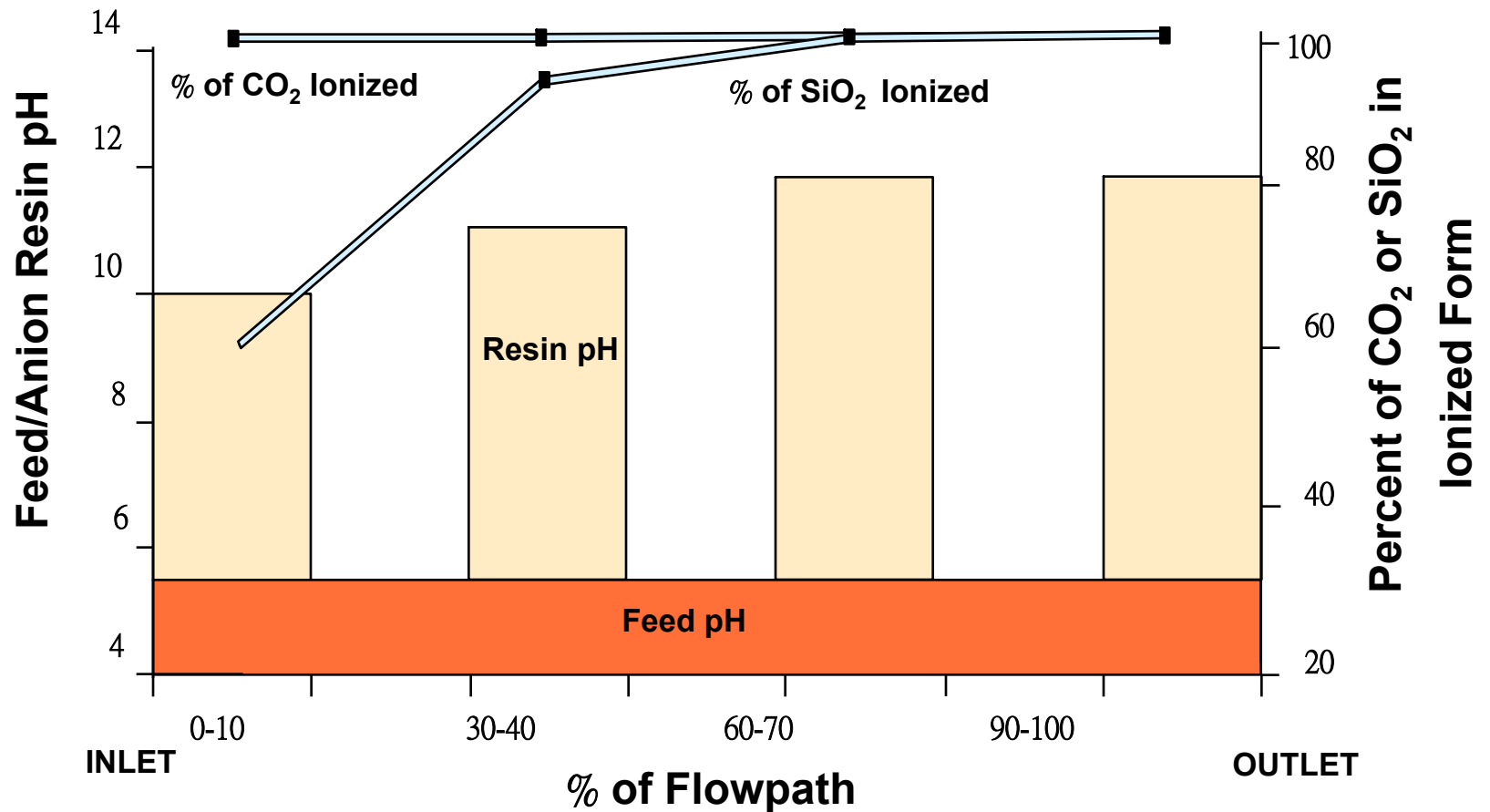
	Feed CO <sub>2</sub> (ppm)	Product CO <sub>2</sub> (ppb)	CO <sub>2</sub> Removal (%)
Semiconductor Plant #1	2.80	10	99.6
Semiconductor Plant #2	4.48	29	99.4
Semiconductor Plant #3	6.52	25	99.6
Semiconductor Plant #4	6.05	10	99.8
Semiconductor Plant #5	6.50	22	99.7

# Summary of Weakly Ionized Species Removal

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- > 99% Silica removal
- > 99% CO<sub>2</sub> removal
- > 96% Boron removal
- > 98% Ammonia removal

# Process Principles



# **EDI Performance**

# EDI Stack Design



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# EDI Performance and Pretreatment



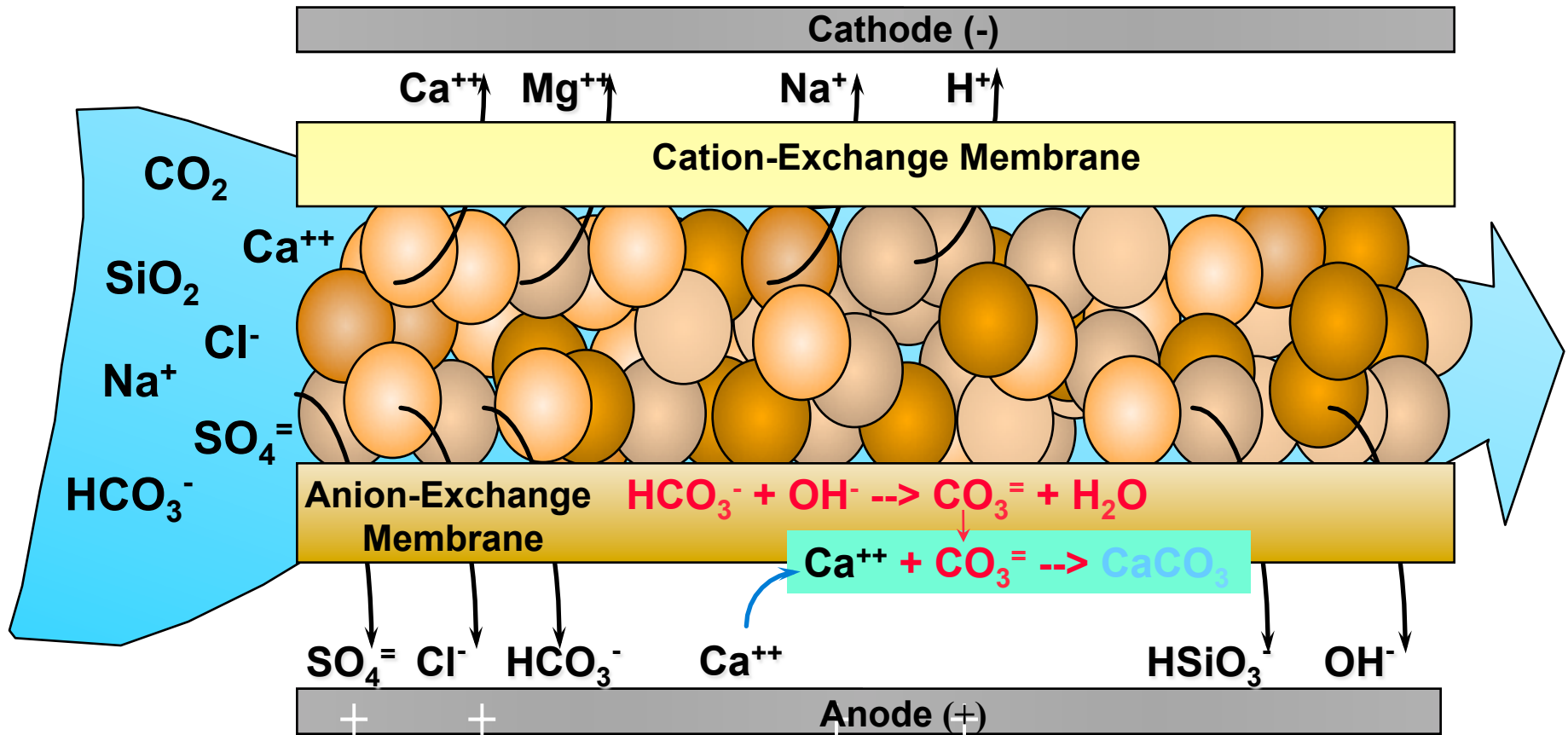
# Performance

- EDI performance effected by:
  - Feed water quality
  - Stack current
  - Water recovery
  - Flow rate
  - Temperature

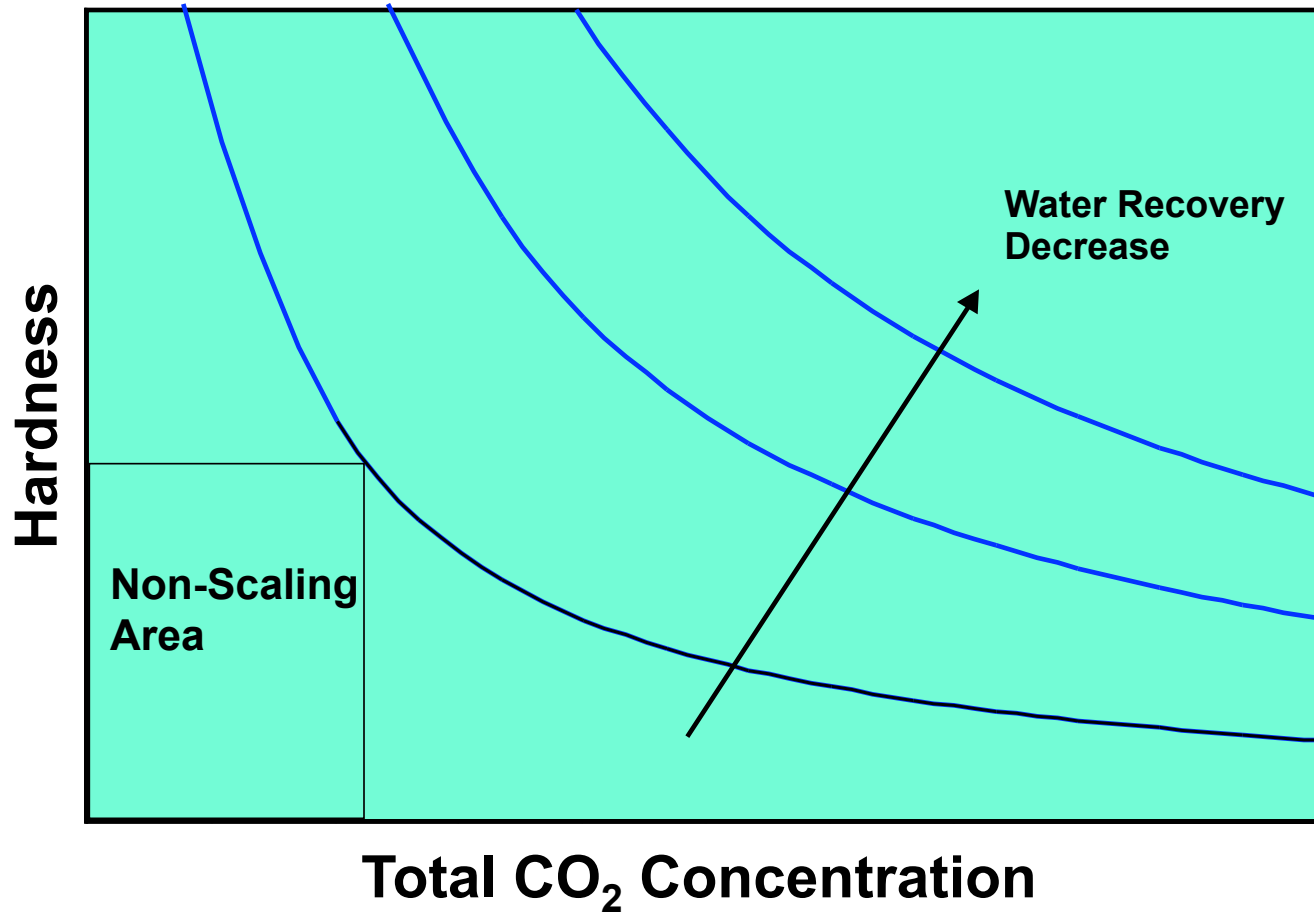
# Feed Water Requirement

- Conductivity: < 40 mS/cm
- Hardness: < 0.25 ppm as CaCO<sub>3</sub>
- TOC: < 0.5 ppm
- Pressure: 20 to 50 psi
- Temperature: 10 to 35°C
- pH: 4 to 10
- Chlorine: < 0.1 ppm
- Fe, Mn, Sulfide: < 0.01 ppm
- CO<sub>2</sub> < 8 ppm

# Scaling in EDI



# Feed Water Requirement



# PERFORMANCE

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- Stack Current
  - Controlled by
    - Stack voltage
    - Brine & electrode stream conductivity
  - Optimum current
    - Too high current
      - Higher scaling potential
      - CO<sub>2</sub> back diffusion
      - Higher power consumption
      - Shorter membrane life

# PERFORMANCE

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- Temperature
  - Better performance at higher temperature
  - Stack pressure drop is sensitive to temperature

# **Feedwater Requirements and Pretreatment**

# Pretreatment

- Minimum pretreatment
  - TFC RO is required to minimize:
    - Scaling
    - Organic fouling
    - Particulate and colloidal plugging
    - Oxidative attack
    - Chemical cleaning

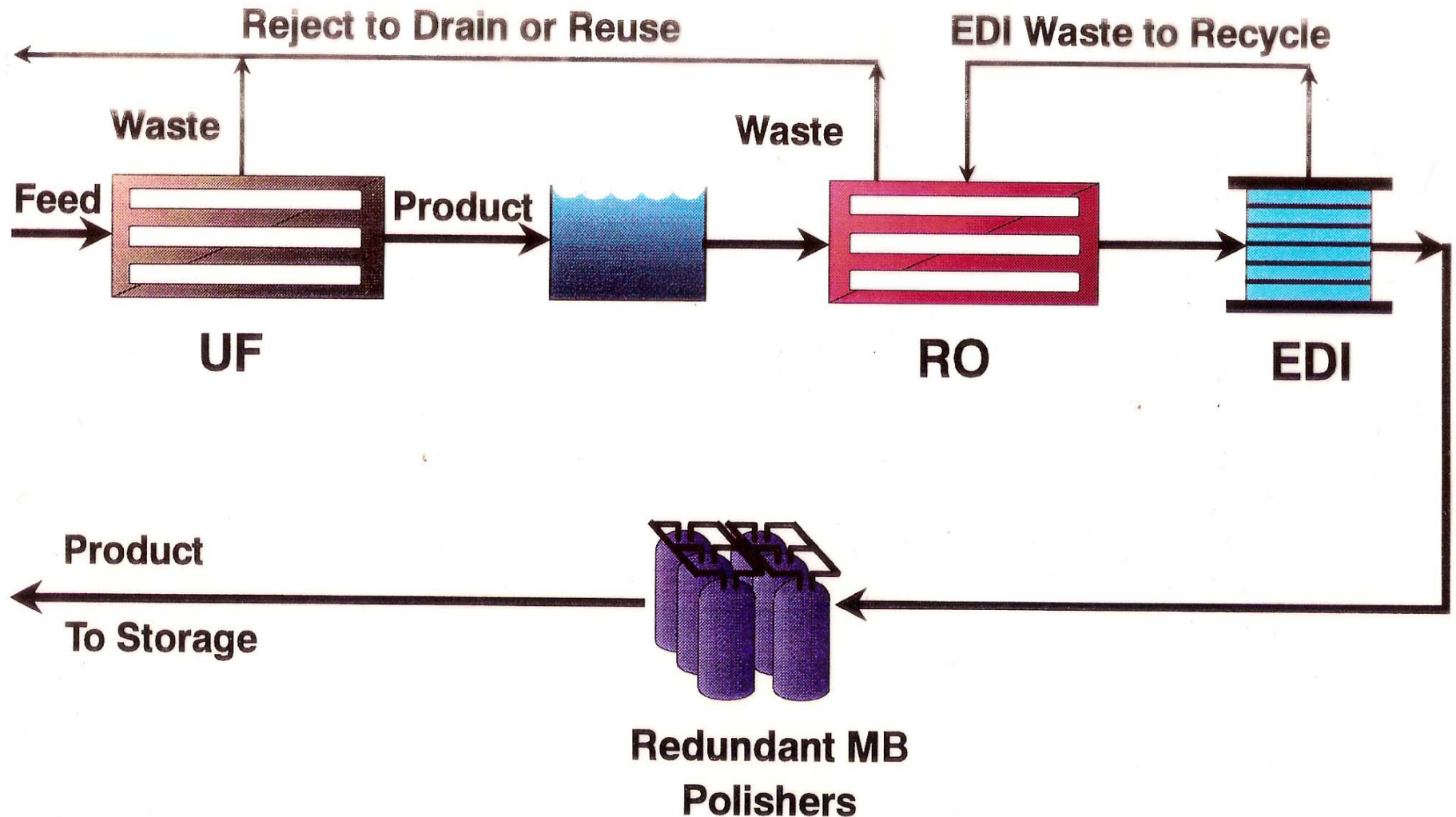


# Pretreatment

- Optional pretreatment
  - Multimedia filter
  - AC filter
  - Degasification
  - UF
  - Softener
  - UV
  - Organic scavenger

# Triple Membrane System

*TMT-II*



# Testing - Organics

- **What is removed?**
  - Organic acids (acetic acid)
  - TMAH(tetramethyl ammonium hydroxide)
  - NMP(N-Methyl Pyrrolidone)
- **What may be removed?**
  - Waco(601?) surfactant
- **What isn't removed?**
  - IPA
- **What may not be removed?**
  - Anti-forming agent
  - Ethylene glycol

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# EDI Operation and Maintenance

# STACK MAINTENANCE

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- Routine Maintenance
- Scaling and Scaling Control
- Fouling and Fouling Control
- Bacteria Control
- Cleaning-In-Place

# STACK MAINTENANCE

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- Routine Maintenance
  - Daily log sheet
  - Visually inspect the stack weekly
  - Hose down any chemical buildup outside the stack
  - Check the stack torque for the first three month, and twice a year thereafter

# STACK MAINTENANCE

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- Stack Scaling
  - Increasing stack resistance
  - Reducing brine flow rate
  - Decreasing silica rejection
  - Product resistivity decline

# STACK MAINTENANCE

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- Scaling Control
  - Brine stream pH control
    - pH3 or lower
  - Softener addition ahead of EDI
  - Reduce water recovery
  - Reliable RO



# STACK MAINTENANCE

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- Stack Fouling
  - Increasing stack resistance
  - Decreasing silica rejection
  - Product resistivity decline
  - Stack pressure drop increase

# STACK MAINTENANCE

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- Fouling Control
  - AC filter
  - UV
  - Organic scavenger
  - Reliable RO

# STACK MAINTENANCE

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- Bacteria Grow in Brine Stream
  - Brine flow decrease
  - High bacteria count in brine stream
- Bacteria Control
  - Sanitize the brine stream periodically
    - 0.1 to 0.2 ppm level of chlorine

# STACK CLEANING

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- Cleaning-in-place (CIP)
  - Continuous (in-flight) brine stream acid CIP
    - pH 1.5 for hours
  - Batch brine stream acid CIP
    - pH1 or lower for more than 30 min.
  - Dilute stream salt & caustic CIP
    - 10% salt
    - pH11
    - 40 C